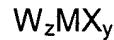


Listing of Claims in the Application as Amended

1. (Original) An alkaline composition for stripping or cleaning integrated circuit substrates, comprising:

(a) one or more bases; and

(b) one or more metal halide compounds of the formula:



where M is a metal selected from the group consisting of Si, Ge, Sn, Pt, P, B, Au, Ir, Os, Cr, Ti, Zr, Rh, Ru, and Sb; X is a halide selected from the group consisting of F, Cl, Br and I; W is selected from the group consisting of H, an alkali or alkaline earth metal, and a metal ion-free hydroxide base moiety; y is a numeral of from 4 to 6 depending on the metal halide; and z is a numeral of from 1, 2 or 3.

2. (Currently amended) A composition according to claim 1 wherein the composition is an aqueous, alkaline composition, the base component (a) is a metal ion-free bases and the base is present in the composition in an amount sufficient to produce a pH of the composition of from about 10 to about 13, and wherein the one or more metal halide compounds is present in the composition an amount of from about 0.5% to about 10% by weight of the composition.

3. (Cancelled)

4. (Cancelled)

5. (Currently amended) The composition of claim 2 1 wherein the base component (a) is selected from the group consisting of ammonium hydroxide, quaternary ammonium hydroxides and diamines.

6. Original) The composition of claim 5 wherein the base component (a) is a tetraalkyl ammonium hydroxide containing alkyl groups of from 1 to 4 carbon atoms.
7. (Currently amended) The composition of claim 3 2 wherein M is selected from the group consisting of Si, Ge, Zr and Sb.
8. (Cancelled)
9. (Cancelled)
10. (Original) The composition of claim 7 wherein the metal halide is selected from the group consisting of H_2SiF_6 , H_2GeF_6 , $((CH_3)_4N)_2GeF_6$, $((CH_3)_4N)_2SiF_6$, $(NH_4)_2SiF_6$ and $(NH_4)_2GeF_6$.
11. (Cancelled)
12. (Cancelled)
13. (Original) The composition of claim 10 wherein the metal halide is H_2SiF_6 .
14. (Cancelled)
15. (Cancelled)
16. (Cancelled)

17. (Original) The composition of claim 2 additionally comprising one or more additional components selected from the group consisting of organic solvents and co-solvents, metal chelating or complexing agents, silicates, fluorides, additional metal corrosion inhibitors, surfactants, titanium residue removal enhancing agents, oxidizing agents and bath stabilizing agents.

18. (Cancelled)

19. (Currently amended) A composition of claim 16 2 comprising tetramethylammonium hydroxide, trans-(1,2-cyclohexylenedinitrilo)tetraacetic acid, hydrogen peroxide, water, and a metal halide compound selected from the group consisting of dihydrogen hexafluorosilicate, dihydrogenhexafluorogermanate, and ammonium hexafluorogermanate and water.

20. (Original) A composition according to claim 19 having a pH of about 11.5.

21. (Cancelled)

22. (Cancelled)

23. (Cancelled)

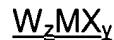
24. (Cancelled)

25. (Currently amended) A method for cleaning semiconductor wafer substrates, comprising:

contacting a semiconductor wafer substrate having a substrate surface for a time and at a temperature sufficient to clean unwanted contaminants and residues from said substrate surface with a composition comprising ~~the composition of claim 1:~~

(a) one or more bases; and

(b) one or more metal halide compounds of the formula:



where M is a metal selected from the group consisting of Si, Ge, Sn, Pt, P, B, Au, Ir, Os, Cr, Ti, Zr, Rh, Ru, and Sb; X is a halide selected from the group consisting of F, Cl, Br and I; W is selected from the group consisting of H, an alkali or alkaline earth metal, and a metal ion-free hydroxide base moiety; y is a numeral of from 4 to 6 depending on the metal halide; and z is a numeral of from 1, 2 or 3.

26. (Currently amended) A method according to claim 25 wherein the composition is a ~~composition of claim 2~~ an aqueous, alkaline composition, the base component (a) is a metal ion-free bases and the base is present in the composition in an amount sufficient to produce a pH of the composition of from about 10 to about 13, and wherein the one or more metal halide compounds is present in the composition an amount of from about 0.5% to about 10% by weight of the composition.

27. (Cancelled)

28. (Cancelled)

29. (Currently amended) The method of claim 25 wherein the ~~composition is a composition of claim 5~~ base component (a) is selected from the group consisting of ammonium hydroxide, quaternary ammonium hydroxides and diamines.

30. (Currently amended) The method of claim 25 29 wherein the composition is a composition of claim 6 base component (a) is a tetraalkyl ammonium hydroxide containing alkyl groups of from 1 to 4 carbon atoms.

31. (Currently amended) The method of claim 25 26 wherein the composition is a composition of claim 7 M is selected from the group consisting of Si, Ge, Zr and Sb.

32. (Cancelled)

33. (Cancelled)

34. (Currently amended) The method of claim 25 31 wherein the composition is a composition of claim 10 metal halide is selected from the group consisting of H_2SiF_6 , H_2GeF_6 , $((CH_3)_4N)_2GeF_6$, $((CH_3)_4N)_2SiF_6$, $(NH_4)_2SiF_6$ and $(NH_4)_2GeF_6$.

35. (Cancelled)

36. (Cancelled)

37. (Currently amended) The method of claim 25 34 wherein the composition is a composition of claim 13 metal halide is H_2SiF_6 .

38. (Cancelled)

39. (Cancelled)

40. (Cancelled)

41. (Currently amended) The method of claim 25 26 wherein the composition is a composition of claim 17 the composition additionally comprises one or more additional components selected from the group consisting of organic solvents and co-solvents, metal chelating or complexing agents, silicates, fluorides, additional metal corrosion inhibitors, surfactants, titanium residue removal enhancing agents, oxidizing agents and bath stabilizing agents.

42. (Cancelled)

43. (Currently amended) The method of claim 25 26 wherein the composition is a composition of claim 19 comprising tetramethylammonium hydroxide, trans-(1,2-cyclohexylenedinitrilo)tetraacetic acid, hydrogen peroxide, water, and a metal halide compound selected from the group consisting of dihydrogen hexafluorosilicate, dihydrogenhexafluorogermanate, and ammonium hexafluorogermanate.

44. (Currently amended) The composition of claim 25 43 wherein the composition is a composition of claim 20 has a pH of about 11.5.

45. (Cancelled)

46. (Cancelled)

47. (Cancelled)

48. (Cancelled)